

Dual N-Channel 30-V (D-S) MOSFET

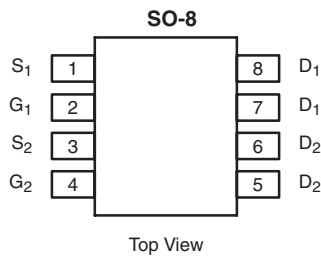
PRODUCT SUMMARY			
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A) ^{a, e}	Q _g (Typ)
30	0.016 at V _{GS} = 10 V	8	19
	0.018 at V _{GS} = 4.5 V	8	
	0.024 at V _{GS} = 2.5 V	8	

FEATURES

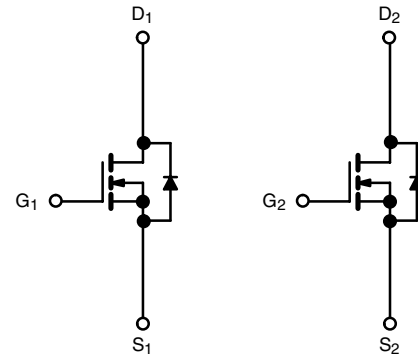
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS tested



RoHS
COMPLIANT



Ordering Information: Si4922BDY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30	V	
Gate-Source Voltage	V _{GS}	± 12	V	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	8 ^e	A
		T _C = 70 °C	8 ^e	
		T _A = 25 °C	8 ^{b, c, e}	
		T _A = 70 °C	6.6 ^{b, c}	
Pulsed Drain Current (10 μs Pulse Width)	I _{DM}	35	A	
Source-Drain Current Diode Current	I _S	T _C = 25 °C	2.5	A
		T _A = 25 °C	1.7 ^{b, c}	
Pulsed Source-Drain Current	I _{SM}	35	A	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	15	mJ
Single-Pulse Avalanche Energy	E _{AS}	11.2		
Maximum Power Dissipation	P _D	T _C = 25 °C	3.1	W
		T _C = 70 °C	2	
		T _A = 25 °C	2 ^{b, c}	
		T _A = 70 °C	1.28 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 50 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit		Unit	
		Typical	Maximum		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 sec	R _{thJA}	50	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	30	40	

Notes:

- Based on T_C = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 sec.
- Maximum under Steady State conditions is 110 °C/W.
- Package Limited.

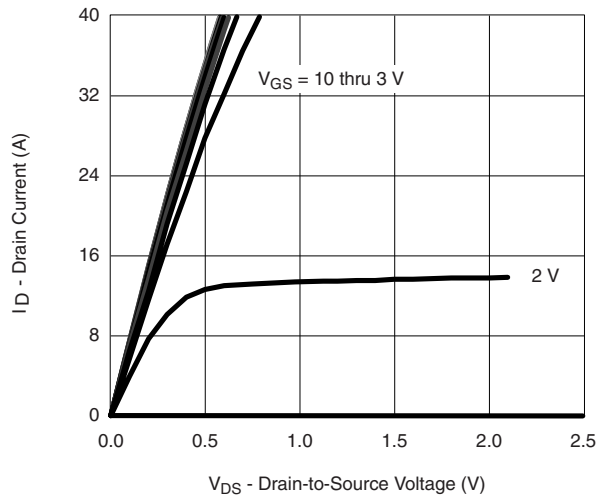
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		35		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 4.6		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.6		1.8	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance ^b	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		0.0135	0.016	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$		0.0145	0.018	
		$V_{GS} = 2.5\text{ V}, I_D = 5\text{ A}$		0.018	0.024	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 5\text{ A}$		30		S
Dynamic^a						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		2070		pF
Output Capacitance	C_{oss}			255		
Reverse Transfer Capacitance	C_{rss}			135		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		41	62	nC
				19	29	
Gate-Source Charge	Q_{gs}	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$		3.5		
Gate-Drain Charge	Q_{gd}			3.7		
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.8	3	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		7	14	ns
Rise Time	t_r			27	41	
Turn-Off Delay Time	$t_{d(off)}$			31	47	
Fall Time	t_f			8	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		13	25	
Rise Time	t_r			53	80	
Turn-Off Delay Time	$t_{d(off)}$			68	102	
Fall Time	t_f			54	81	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			2.5	A
Pulse Diode Forward Current ^a	I_{SM}				35	
Body Diode Voltage	V_{SD}	$I_S = 1.7\text{ A}$		0.77	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		32	48	ns
Body Diode Reverse Recovery Charge	Q_{rr}			21	32	nC
Reverse Recovery Fall Time	t_a			13		ns
Reverse Recovery Rise Time	t_b			19		

Notes:

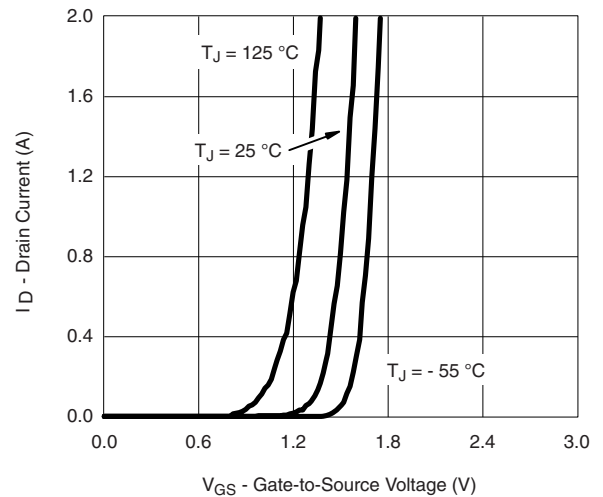
- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

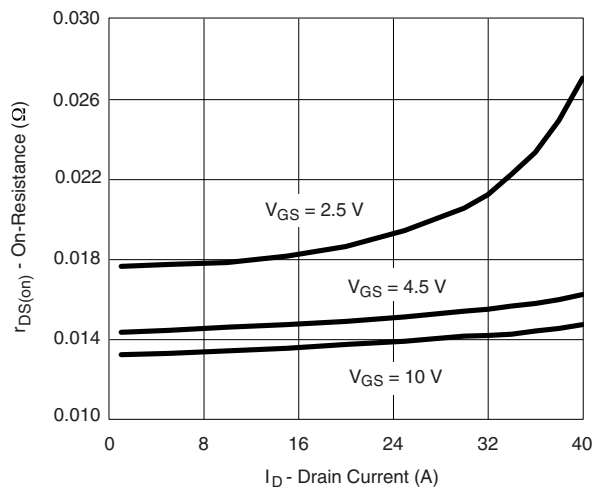
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



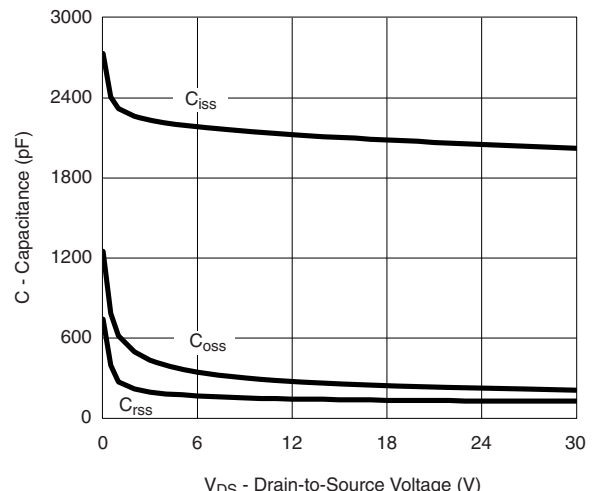
Output Characteristics



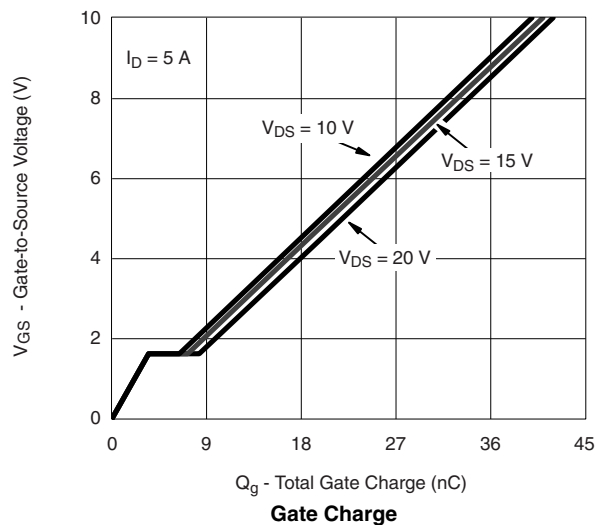
Transfer Characteristics



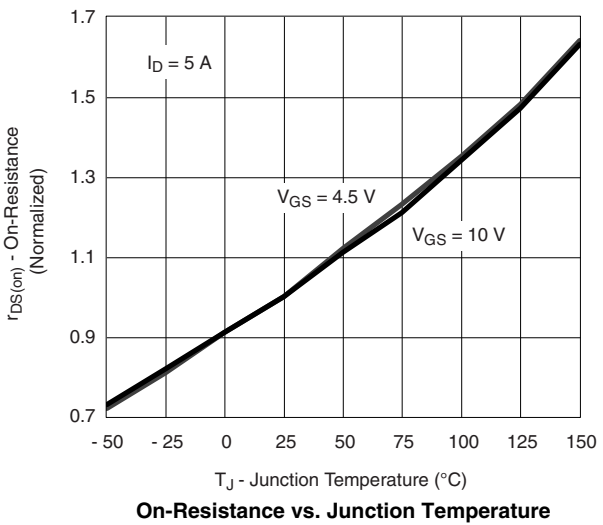
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



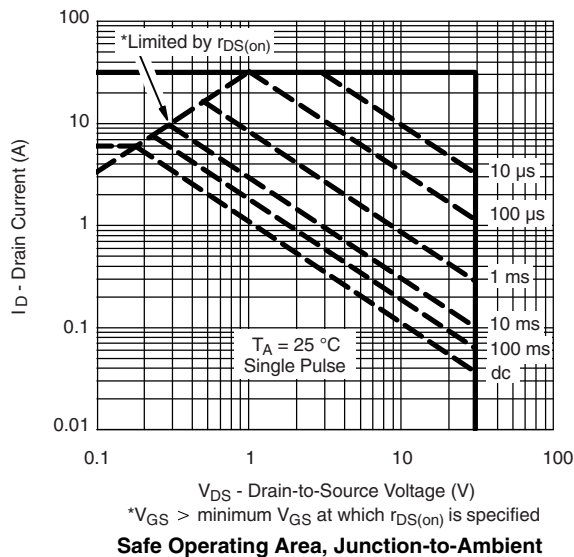
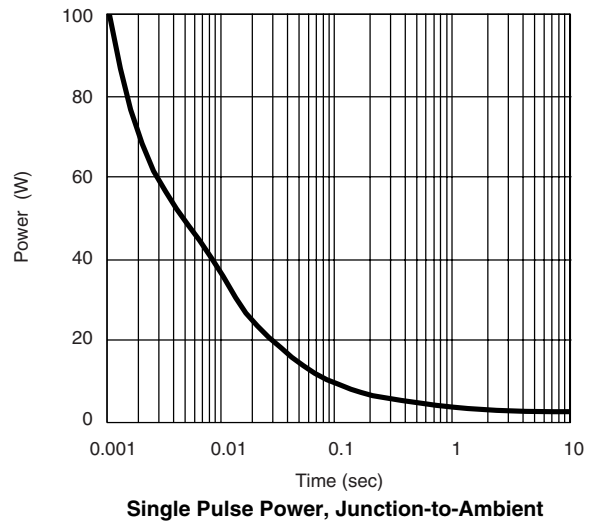
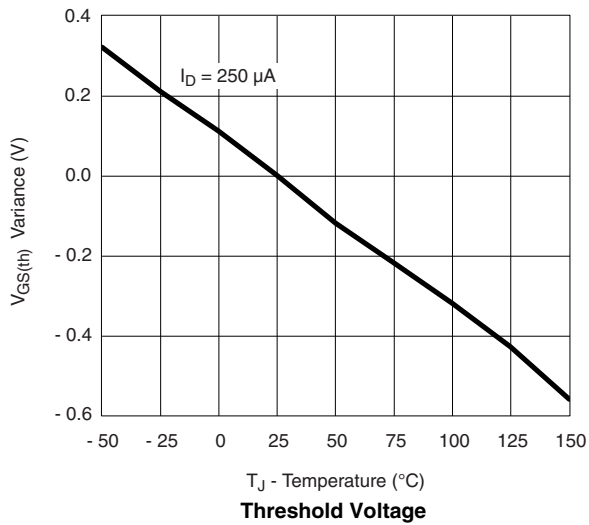
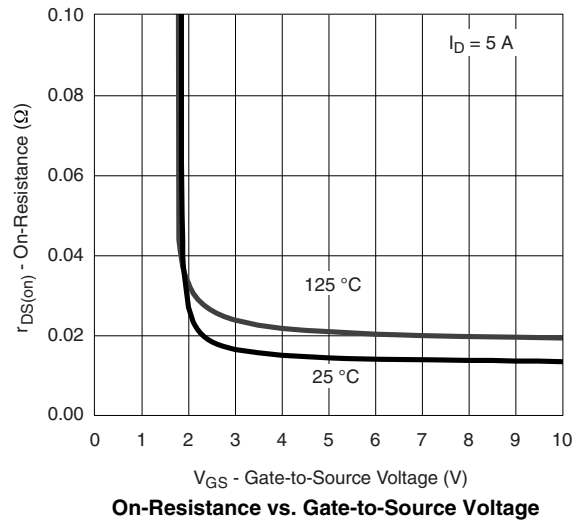
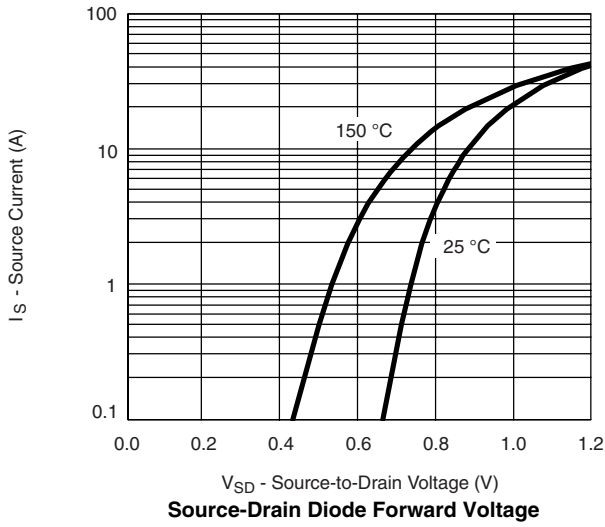
Gate Charge



On-Resistance vs. Junction Temperature

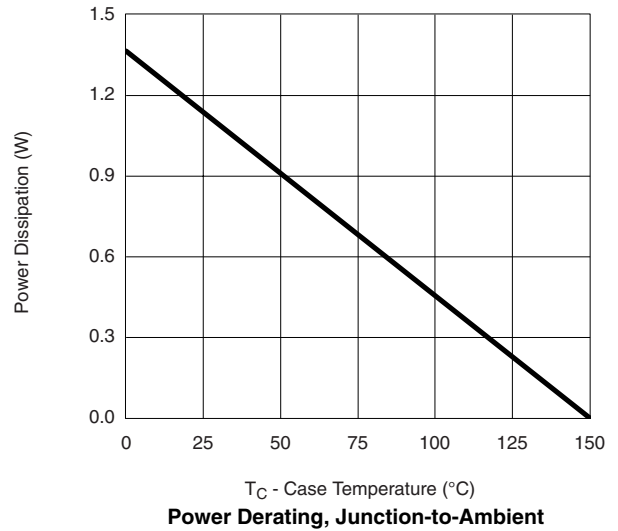
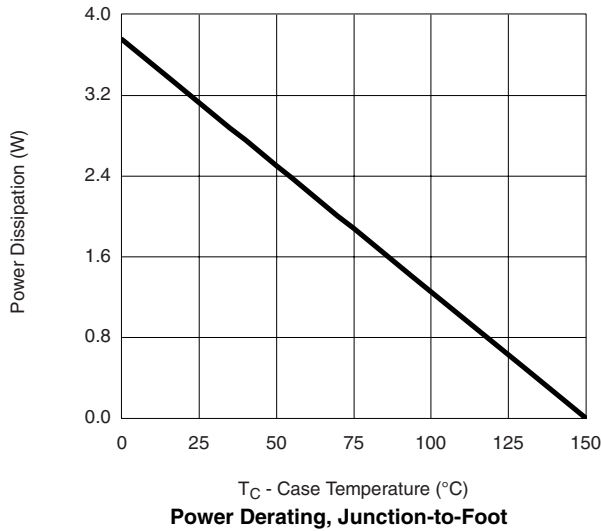
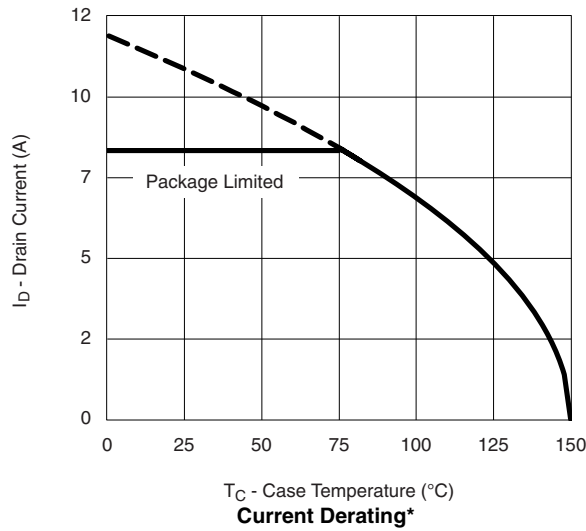


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





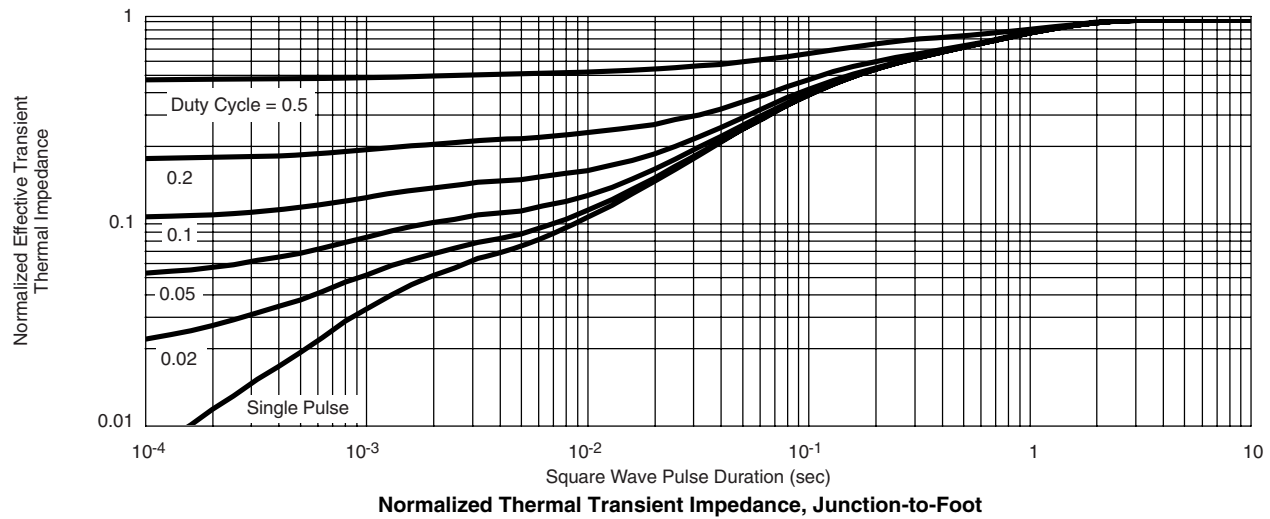
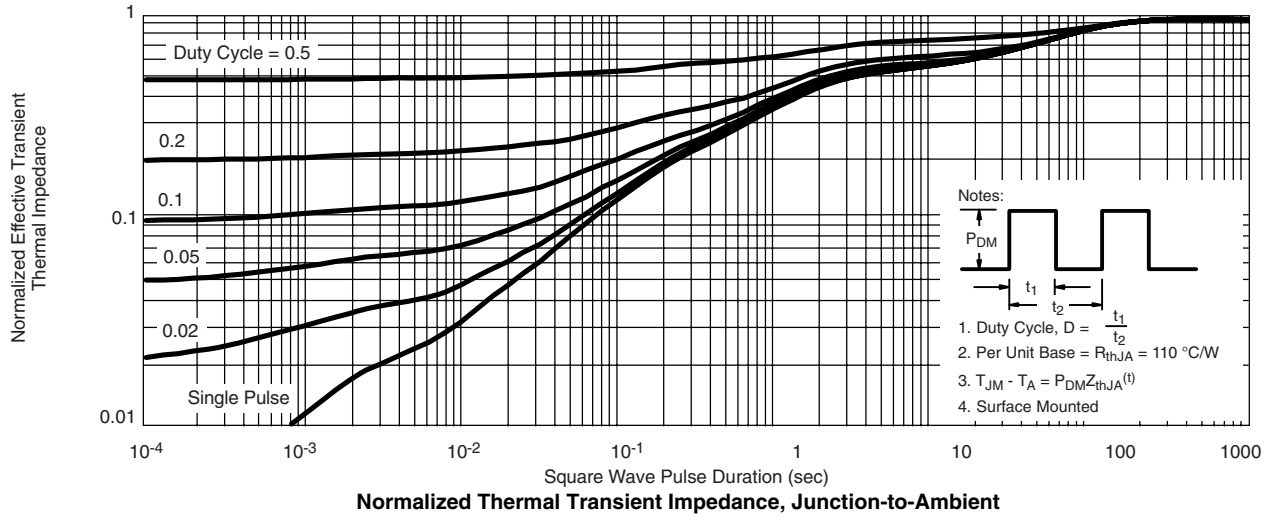
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



*The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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